

VERIFICATION OF TRANSLATION

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declare that I am well acquainted with both the Japanese and English languages, and that the attached is an accurate partial translation, to the best of my knowledge and ability, of Japanese Patent Application Publication No. H9-172063 (translation of first and last pages only), published June 30, 1997.

I further declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the above-captioned application or any patent issued thereon.

Signature _____



Yukiko Toyoda Buntin

Date _____

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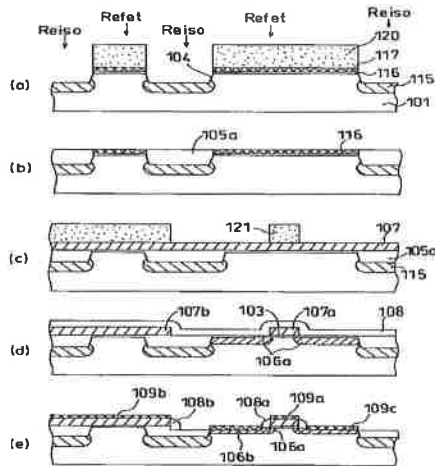
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(54) Title of Invention

SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

- 4 溝部
 5 シリコン酸化膜 (絶縁膜)
 5a 溝型素子分離
 6a 低濃度ソース・ドレイン領域
 6b 高濃度ソース・ドレイン領域
 7 ポリシリコン膜 (導電膜)
 7a ゲート電極
 7b ゲート配線
 8 シリコン酸化膜
 8a 電極部サイドウォール
 8b 配線部サイドウォール
 8c 段差部サイドウォール
 9a 上部ゲート電極
 9b 上部ゲート配線
 9c ソース・ドレイン電極
 11 層間絶縁膜
 12 第1層目金属配線
 13 コンタクト部
 15 チャネルストップ領域
 16 シリコン酸化膜
 17 シリコン窒化膜 (エッチングストップ膜)
 20, 21 フォトリジスト膜
 【手続補正2】
 【補正対象書類名】図面
 【補正対象項目名】図7
 【補正方法】変更
 【補正内容】

【図7】



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